

## Supporting Information

### **High-Detectivity Panchromatic Photodetectors to the Near Infrared Region Based on a Dimeric Porphyrin Small Molecule**

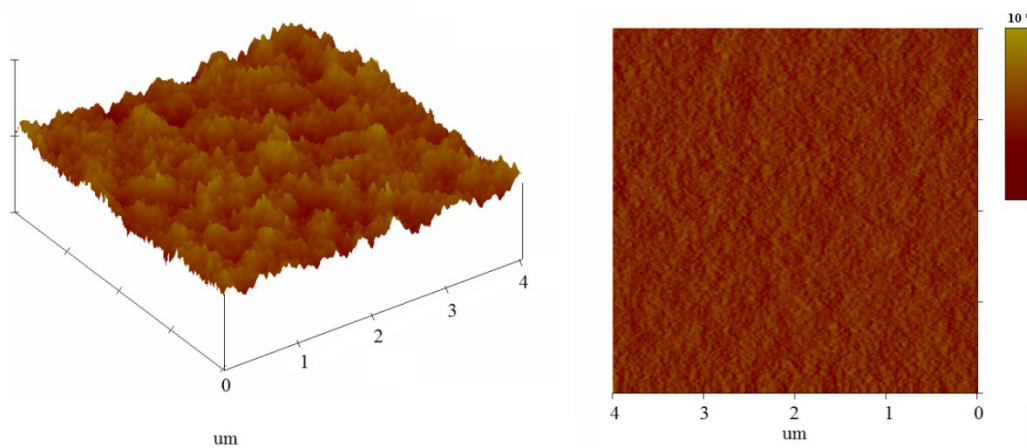
Liangang Xiao,<sup>a#</sup> Song Chen,<sup>b#</sup> Xuebin Chen,<sup>a</sup> Xiaobin Peng,<sup>\*a</sup> Yong Cao,<sup>a</sup> and Xunjin Zhu<sup>\*b</sup>

a. Institute of Polymer Optoelectronic Materials and Devices, State Key Laboratory of Luminescent Materials and Devices, South China University of Technology, 381 Wushan Road, Guangzhou 510640, China

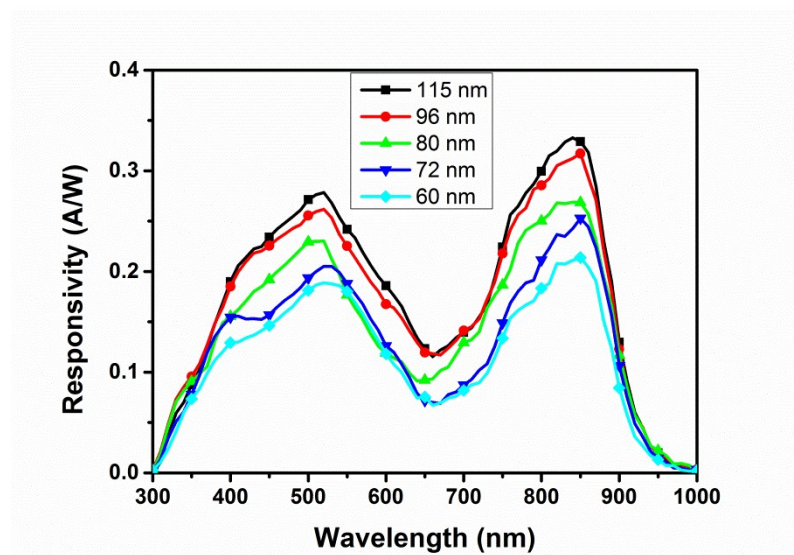
b. Department of Chemistry and Institute of Molecular Functional Materials, Hong Kong Baptist University, Waterloo Road, Kowloon Tong, Hong Kong, China

# L. X and S. C contribute equally to the work.

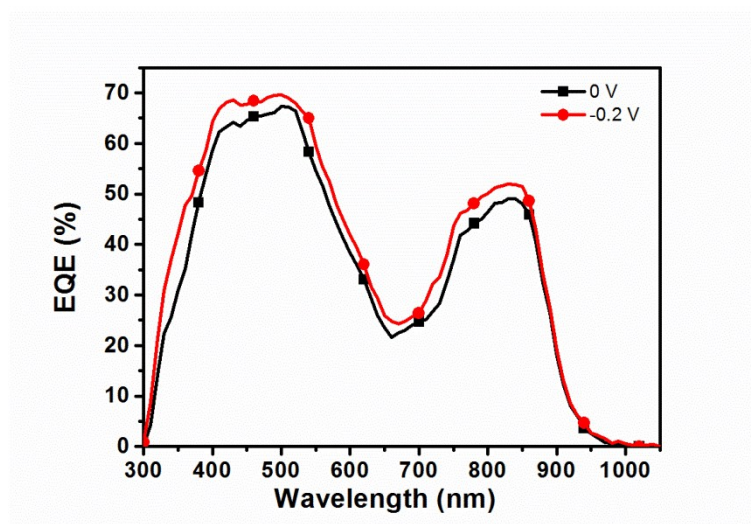
\*Email - chxbpeng@scut.edu.cn



**Figure S1.** AFM height (left) and phase images (right) of the blend films with thermal annealing treatment. ( $4 \times 4 \mu\text{m}$ )



**Figure S2.** Responsivity curves of the organic photodetectors with different active layer thickness.



**Figure S3.** External quantum efficiency spectra of the NIR OPDs with 115 nm active layers under 0 and -0.2 V bias.